## Piezoresistance Constants of *n*-Type InAs

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A measurement of the piezoresistance constants of n-type InAs as a function of temperature from 77°K to  $300^{\circ}$ K has been made. From the small magnitude found for the three constants throughout the temperature range investigated, it is concluded that the results of this experiment are consistent with a spherical conduction-band model for InAs.

MEASUREMENT of the piezoresistance constants of single-crystal specimens of n type InAs as a function of temperature from 77°K to 300°K has been made. The experimental arrangement is identical with that described earlier.<sup>1,2</sup> The conventional notation and terminology are used below in reporting the data <sup>1-3</sup>

Single-crystal specimens were cut from large grains of a zone-refined polycrystalline ingot of InAs. The samples were oriented by Laue back-reflection x-ray pictures. The error in orientation was about 2°. A Hall measurement at 77°K gave an electron concentration of  $1.1 \times 10^{17}$  cm<sup>-3</sup>. The resistivity of the samples was  $2.4 \times 10^{-3}$  ohm-cm at 77°K. The samples were extrinsic throughout the temperature range investigated. The piezoresistance constants  $\Pi_{11}$ ,  $\Pi_{12}$ , and  $\Pi_{44}$  were determined by performing "longitudinal"1-3 measurements on samples oriented along the [110] or [111] directions and a "transverse"1-3 measurement with current and stress in the  $\lceil 100 \rceil$  and  $\lceil 011 \rceil$  directions, respectively. The tensile stress used was approximately  $2 \times 10^7$  dynes cm<sup>-2</sup>. Since the resistivity of the samples was very low, the stress-induced change in the resistivity was also very small, corresponding to voltage changes in the range 0.2 to 1 microvolt. Consequently, the errors in the  $\Pi$  constants are relatively large (See Table I). Fortunately, the relative order of magnitude for the constants is all that is needed for the discussion below. Table I presents the piezoresistance constants at 300°K and 77°K. The values in Table I have not been corrected for dimensional changes<sup>3</sup> since the elastic constants of InAs are not available. By comparison with InSb,<sup>1,2</sup> it is estimated that dimensional effects will introduce an additional error of the order

TABLE I. Piezoresistance constants of n-type InAs at 300°K and 77°K.

	300°K	77°K
$ \begin{array}{l} \Pi_{11}({\rm cm}^2{\rm dyn}e^{-1}) \\ \Pi_{12}({\rm cm}^2{\rm dyn}e^{-1}) \\ \Pi_{44}({\rm cm}^2{\rm dyn}e^{-1}) \end{array} $	$ \begin{array}{c} (-5\pm3)\times10^{-12} \\ (-5\pm3)\times10^{-12} \\ (0\pm3)\times10^{-12} \end{array} $	$\begin{array}{c} (-3\pm3)\times10^{-12} \\ (-8\pm3)\times10^{-12} \\ (-1\pm3)\times10^{-12} \end{array}$

<sup>1</sup> A. J. Tuzzolino, Phys. Rev. 109, 1980 (1958).
 <sup>2</sup> R. F. Potter, Phys. Rev. 108, 652 (1957).
 <sup>3</sup> C. S. Smith, Phys. Rev. 94, 42 (1954).

of  $\pm 2 \times 10^{-12}$  cm<sup>2</sup> dyne<sup>-1</sup> into the quantities reported in Table I. It is evident that the piezoresistance effect is small and that the shear constants  $^{1\!-\!3}$   $\Pi_{11}$  $-\Pi_{12}$  and  $\Pi_{44}$  are very nearly zero.

Recent theoretical<sup>4,5</sup> and experimental<sup>6,7</sup> studies of the conduction band of zinc-blende type crystals indicate that the conduction band of InAs, in particular, is isotropic, i.e., the constant-energy surfaces for the electrons are spheres. The theory of the piezoresistance effect for such a band structure<sup>8,9</sup> predicts a zero, or very small, magnitude for the shear constants over the complete temperature range. The small values found for the shear constants suggest such a band structure. Recently, this prediction has been verified experimentally for the compound InSb.<sup>2</sup> For example, in the extrinsic temperature range the shear constants for *n*-type InSb, which is known to have spherical energy surfaces for electrons,<sup>5,10</sup> are independent of temperature and are approximately two orders of magnitude smaller than for p-type InSb,<sup>1,2</sup> which is expected to have "large"<sup>5,8,9</sup> temperature-dependent values for the shear constants. The magnitudes of the  $\Pi$  constants found for the extrinsic *n*-type InAs reported here are smaller than, but of the same order as, those found for extrinsic n-type InSb.<sup>2</sup> In addition, no temperature dependence was found for the  $\Pi$ constants for InAs from 77°K to 300°K, within experimental error. Therefore, by comparing the magnitude of the II constants in the extrinsic range with theoretical predictions and the corresponding magnitudes for InSb, it is concluded that the results of this experiment are consistent with a spherical conduction-band model for InAs.

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- <sup>4</sup>G. Dresselhaus, Phys. Rev. 100, 580 (1955).
  <sup>5</sup>E. O. Kane, J. Phys. Chem. Solids 1, 249 (1956).
  <sup>6</sup>R. J. Sladek, Westinghouse Research Laboratory Scientific Paper 8-1038-P6, 1956 (unpublished).
  <sup>7</sup>F. Stern and R. M. Talley, Phys. Rev. 100, 1638 (1955).
  <sup>8</sup>C. Herring, Bell System Tech. J. 34, 237 (1955).
  <sup>9</sup>E. N. Adams, Chicago Midway Laboratories Technical Report, CML-TN-P8, 1954 (unpublished).
  <sup>10</sup> Dresselhaus, Kip, Kittel, and Wagner, Phys. Rev. 98, 556 (1955). (1955).